

Supplementary Materials: Direct Inkjet Printing of Silver Source/Drain Electrodes on an Amorphous InGaZnO Layer for Thin-Film Transistors

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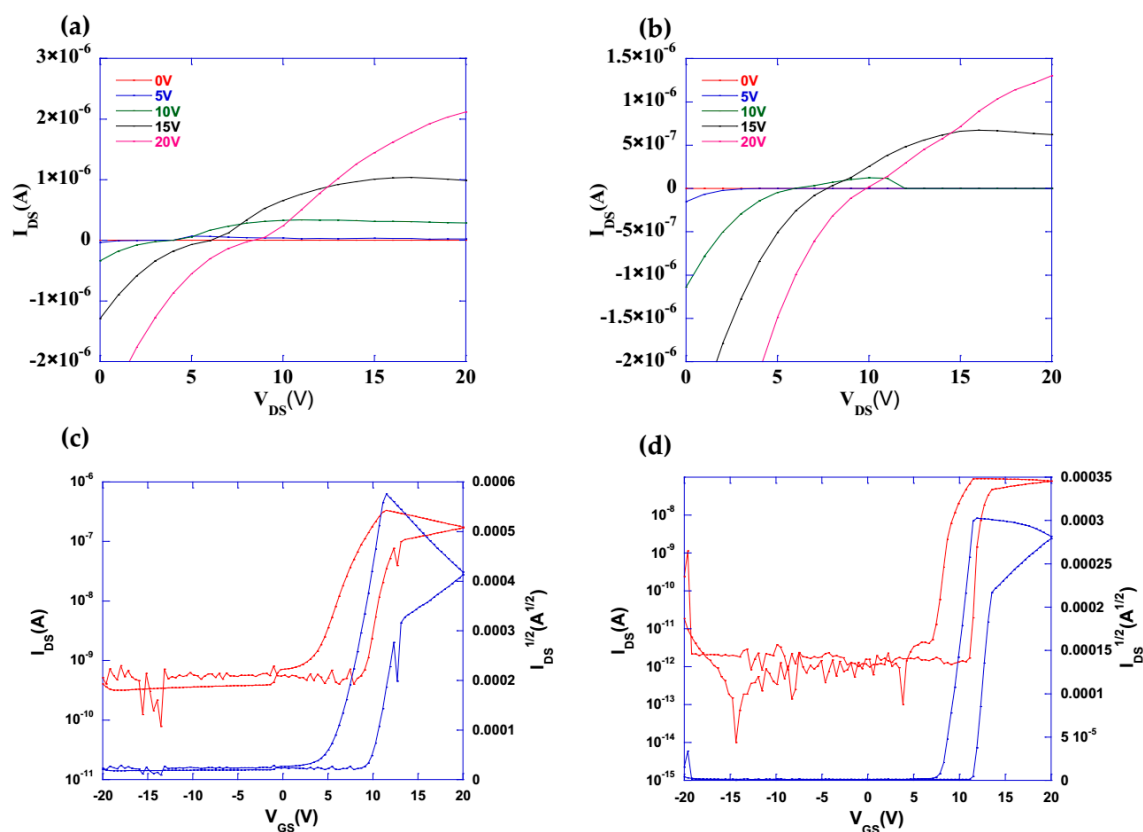


Figure S1. Output characteristic curves (I_{DS} – V_{DS}) and transfer characteristic curve (I_{DS} – V_{GS}) of manufactured a-IGZO TFTs at different printing substrate temperatures. (a) 40 °C; (b) 50 °C; (c) 40 °C; (d) 50 °C. V_{GS} is varied from 20 to –20 V with $V_{DS} = 10.1$ V.

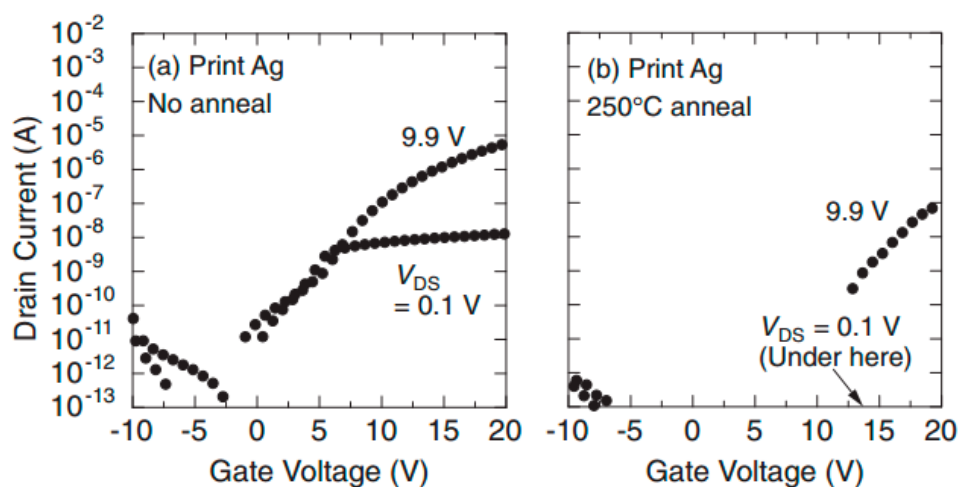


Figure S2. Transfer characteristic curve (I_{DS} – V_{GS}) of devices Yoshihiro et al. had reported.

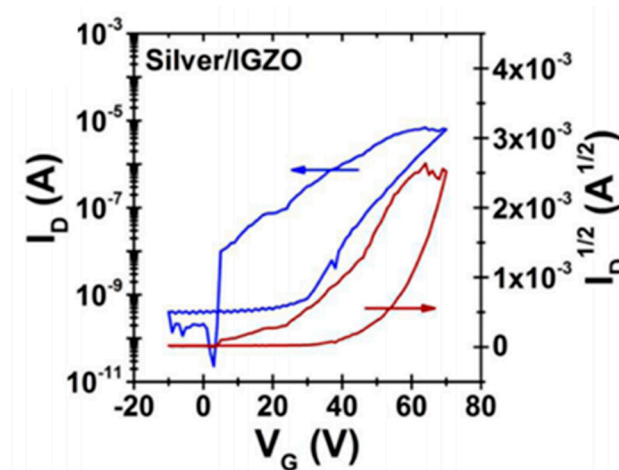


Figure S3. Transfer characteristic curve (I_{DS} - V_{GS}) of devices Ethan et al. had reported.